

Amendments to the Specification:

Please replace paragraph 39 on page 9 with the following amended paragraph.

[0039] The gates 410 and 420 are also effectively separated by fin 210 and may be separately biased (via respective gate electrodes 510 and 520) based on the particular circuit requirements of device 100. This separate double gate structure provides increased flexibility during circuit design, as opposed to conventional FinFETs which include a single ~~gat~~ gate connection.